

International
IOR Rectifier

IRFK6H150, IRFK6J150

Isolated Base Power HEX-pak™ Assembly - Parallel Chip Configuration

- High Current Capability.
- UL recognised E78996.
- Electrically Isolated Base Plate.
- Easy Assembly into Equipment.

Description

The HEX-pak™ utilises the well-proven HEXFET™ die, combining low on-state resistance with high transconductance. These superior technology die are assembled by state of the art techniques into the TO-240 package, featuring 2.5kV rms isolation and solid M5 screw connections. The small footprint means the package is highly suited to power applications where space is a premium. Available in two versions, IRFK.H... for fast switching and IRFK.J... for oscillation sensitive applications.

$$V_{DS} = 100V$$

$$R_{DS(on)} = 10m\Omega$$

$$I_D = 150A$$

Absolute Maximum Rating

	Parameter	Max.	Units
$I_D @ T_C=25^\circ C$	Continuous Drain Current	150	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current	120	A
I_{DM}	Pulse Drain Current	720	A ①
$P_D @ T_C=25^\circ C$	Maximum Power Dissipation	625	W
V_{GS}	Gate-to-Source Voltage	20	V
V_{INS}	R.M.S. Isolation Voltage, circuit to base	2.5	kV
T_J	Operating Junction Temperature Range	-40 to 150	$^\circ C$
T_{STG}	Storage Temperature Range	-40 to 150	$^\circ C$

Thermal and Mechanical Specifications

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	-	-	0.20	K/W ②
R_{thCS}	Case-to-Sink, smooth & greased surface	-	0.1	-	K/W
T	Mounting Torque +10%				③
	HEXpak to Heatsink	-	5	-	Nm
	Busbar to HEXpak	-	3	-	Nm
wt	Approximate Weight	-	140	-	g
		-	5	-	oz

Notes:

- ① - Repetitive Rating: Pulse width limited by maximum junction temperature see figure 8.
- ② - Per Module.
- ③ - A mounting compound is recommended and the torque should be rechecked after a period of three hours to allow for the spread of the compound.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
B _{VDS}	Drain-to-Source Breakdown voltage	100	-	-	V	V _{GS} =0V, I _D =1.0mA	
R _{DS(on)}	Static Drain-to-Source On-State Resistance	-	8	10	mΩ	V _{GS} =10V, I _D =120A	
I _{D(on)}	On-State Drain Current	150	-	-	A	V _{DS} > I _{D(on)} × R _{DS(on)} max, V _{GS} =10V	
V _{GS(th)}	Gate Threshold Voltage	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =1.5mA	
g _{fs}	Forward Transconductance ④	75	120	-	S	V _{DS} > 50V, I _D =120A	
I _{DSS}	Zero Gate Voltage Drain Current	-	-	1.5	mA	V _{DS} =V _{DS} max, V _{GS} =0V	
		-	-	6.0	mA	V _{GS} =10V, T _C =125°C, V _{DS} =V _{DS} max x 0.8	
I _{GSS}	Gate-to-Source Leakage Forward	-	-	600	nA	V _{GS} =20V	
I _{GSS}	Gate-to-Source Leakage Reverse	-	-	-600	nA	V _{GS} =-20V	
Q _g	Total Gate Charge	-	530	750	nC	I _D =150A, V _{GS} =10V,	
Q _{gs}	Gate-to-Source Charge	-	100	150	nC	V _{DS} =V _{DS} max x 0.8	
Q _{gd}	Gate-to-Drain ("Miller") Charge	-	250	350	nC		
t _{d(on)}	Turn-on Delay Time	IRFK6H150	-	105	-	ns	V _{DD} =40V, I _D =120A, V _{GS} =10V, R _{SOURCE} =3.3Ω
		IRFK6J150	-	120	-	ns	
t _r	Rise Time	IRFK6H150	-	460	-	ns	
		IRFK6J150	-	570	-	ns	
t _{d(off)}	Turn-off Delay Time	IRFK6H150	-	300	-	ns	
		IRFK6J150	-	400	-	ns	
t _f	Fall Time	IRFK6H150	-	150	-	ns	
		IRFK6J150	-	240	-	ns	
L _{DS}	Drain-to-Source Inductance	-	18	-	nH		
C _{iss}	Input Capacitance	-	11.0	-	nF	V _{GS} =0V, V _{DS} =25V,	
C _{oss}	Output Capacitance	-	6.0	-	nF	f=1.0MHz	
C _{rss}	Reverse Transfer Capacitance	-	5.0	-	nF		
	Linear Derating Factor	-	-	5	W/K		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	150	A	
I_{SM}	Pulsed Source Current (Body Diode)	-	-	665	A	
V_{SD}	Diode Forward Voltage	-	-	2.5	V	$V_{GS}=0V, I_S=150A, T_C=25^\circ\text{C}$
t_{rr}	Reverse Recovery Time	90	190	390	ns	$di/dt=400A/\mu s, T_J=150^\circ\text{C}$
Q_{rr}	Reverse Recovered Charge	4.5	10.0	20.0	μC	$I_S=150A$

Notes:

④ - Pulse Width $\leq 300\mu s$; Duty cycle $\leq 2\%$.

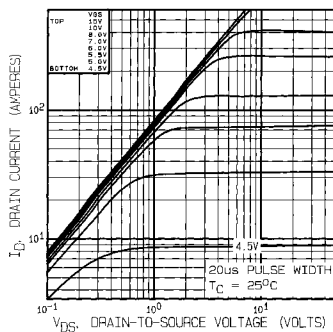


Fig 1. Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

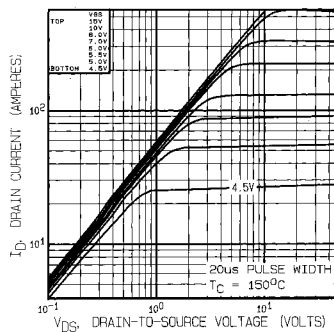


Fig 2. Typical Output Characteristics,
 $T_C=150^\circ\text{C}$

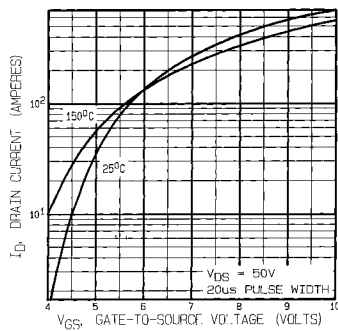


Fig 3. Typical Transfer Characteristics

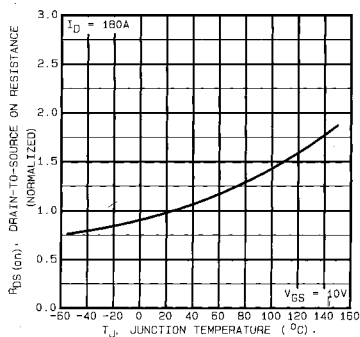


Fig 4. Normalized On-Resistance Vs.
Temperature

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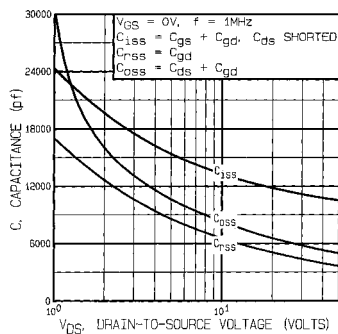


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

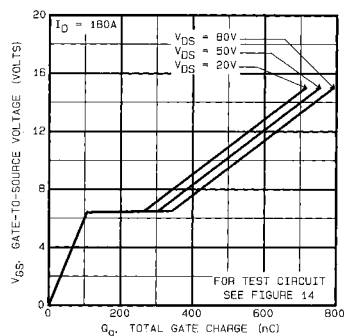


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

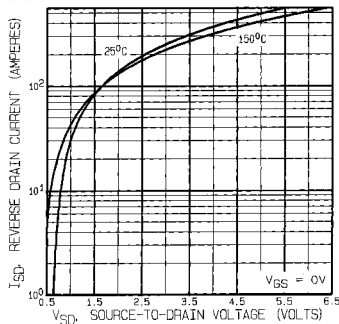


Fig 7. Typical Source-Drain Diode Forward Voltage

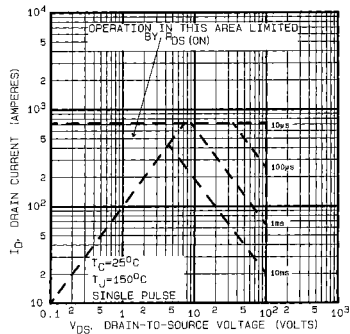


Fig 8. Maximum Safe Operating Area

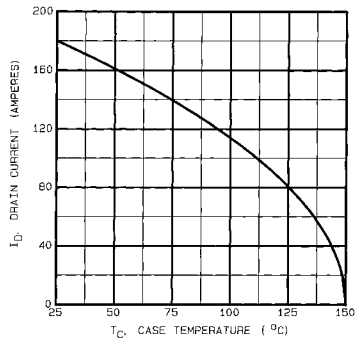


Fig 9. Maximum Drain Current Vs. Case Temperature

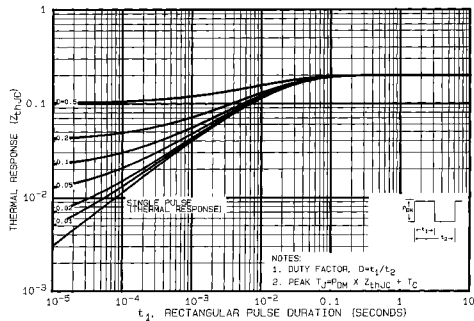


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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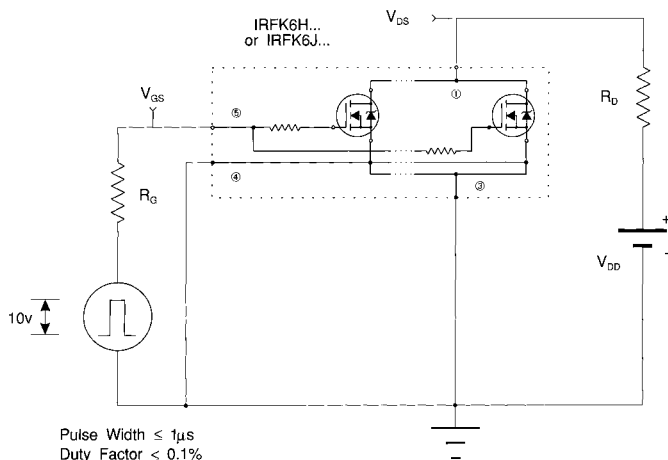


Fig 11a. Switching Time Test Circuit

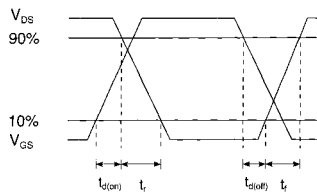
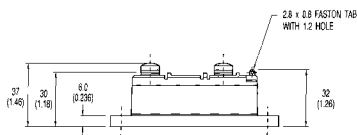
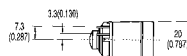
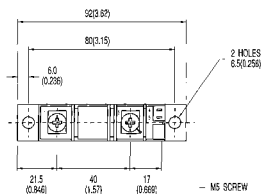
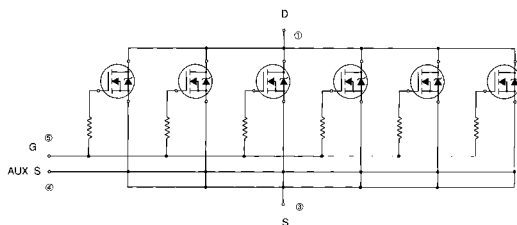


Fig 11b. Switching Time Waveforms



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Circuit Configuration and Outline



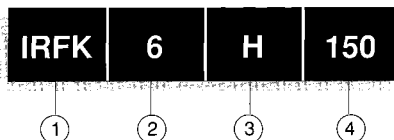
NOTE:
DEVICE IS SUPPLIED WITH
AUXILIARY LEADS 200(7.87) LONG

All dimensions in millimetres (inches)

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Part Numbering



1. - HEX-pak Module.
2. - Number of HEXFETs in parallel.
3. - H - Fast switching.
4. - J - Oscillation resistant for sensitive applications.
4. - Voltage code:-

054	-	60V
150	-	100V
250	-	200V
350	-	400V
450	-	500V
C50	-	600V

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In the interest of product improvement INTERNATIONAL RECTIFIER reserves the right to change specifications at any time without notice.

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